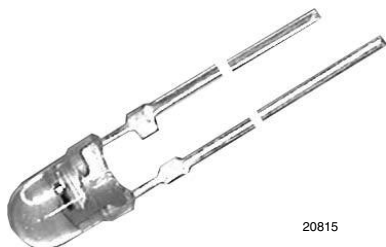


Silicon NPN Phototransistor, RoHS Compliant



DESCRIPTION

BPW85 is a silicon NPN phototransistor with high radiant sensitivity in clear, T-1 plastic package. It is sensitive to visible and near infrared radiation.

FEATURES

- Package type: leaded
- Package form: T-1
- Dimensions (in mm): $\varnothing 3$
- High photo sensitivity
- High radiant sensitivity
- Suitable for visible and near infrared radiation
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 25^\circ$
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

APPLICATIONS

- Detector in electronic control and drive circuits

PRODUCT SUMMARY			
COMPONENT	I_{ca} (mA)	φ (deg)	$\lambda_{0.1}$ (nm)
BPW85A	0.8 to 2.5	± 25	450 to 1080
BPW85B	1.5 to 4	± 25	450 to 1080
BPW85C	3 to 8	± 25	450 to 1080

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPW85A	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1
BPW85B	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1
BPW85C	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	5	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10$ ms	I_{CM}	100	mA
Power dissipation	$T_{amb} \leq 55$ °C	P_V	100	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 100	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	$t \leq 3$ s, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction/ambient	Connected with Cu wire $\varnothing 0.14$ mm ²	R_{thJA}	450	K/W

Note

$T_{amb} = 25$ °C, unless otherwise specified

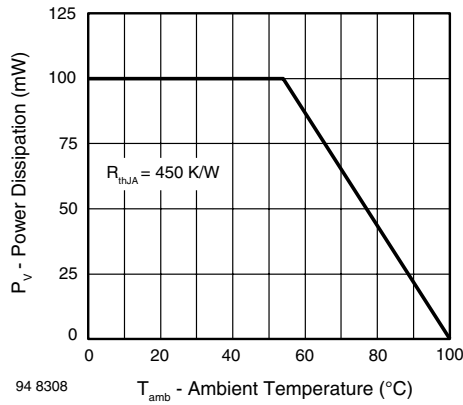


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	$I_C = 1 \text{ mA}$	$V_{(BR)CEO}$	70			V
Collector emitter dark current	$V_{CE} = 20 \text{ V}, E = 0$	I_{CEO}		1	200	nA
Collector emitter capacitance	$V_{CE} = 5 \text{ V}, f = 1 \text{ MHz}, E = 0$	C_{CEO}		3		pF
Angle of half sensitivity		ϕ		± 25		deg
Wavelength of peak sensitivity		λ_p		850		nm
Range of spectral bandwidth		$\lambda_{0.1}$		450 to 1080		nm
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, I_C = 0.1 \text{ mA}$	V_{CEsat}			0.3	V
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t_{on}		2.0		μs
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t_{off}		2.3		μs
Cut-off frequency	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	f_c		180		kHz

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_{CE} = 5 \text{ V}$	BPW85A	I_{ca}	0.8		2.5	mA
		BPW85B	I_{ca}	1.5		4.0	mA
		BPW85C	I_{ca}	3.0		8.0	mA

BASIC CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

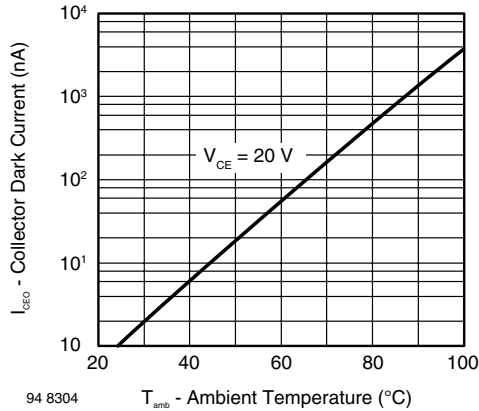


Fig. 2 - Collector Dark Current vs. Ambient Temperature

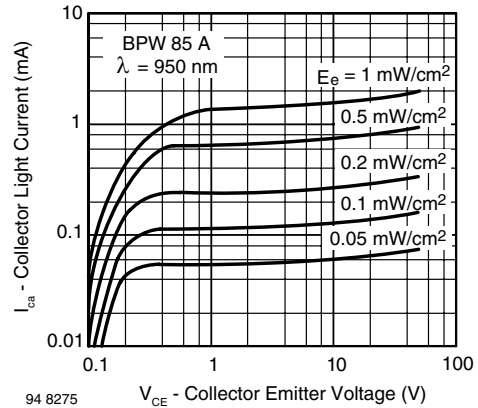


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

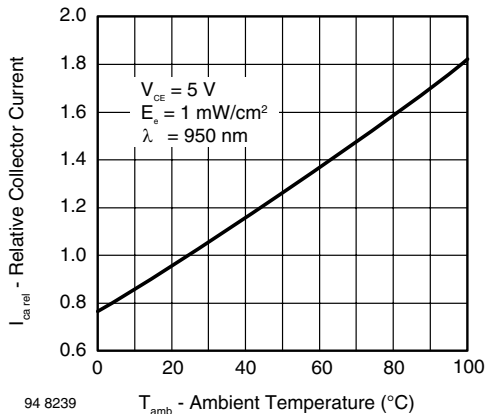


Fig. 3 - Relative Collector Current vs. Ambient Temperature

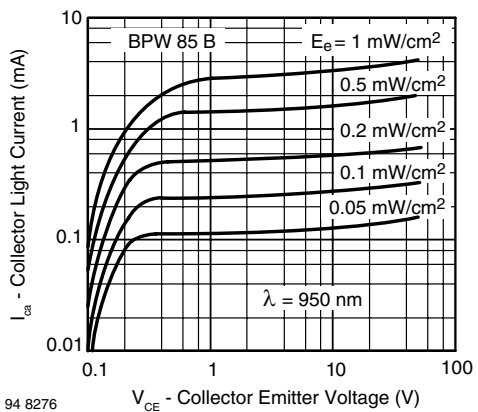


Fig. 6 - Collector Light Current vs. Collector Emitter Voltage

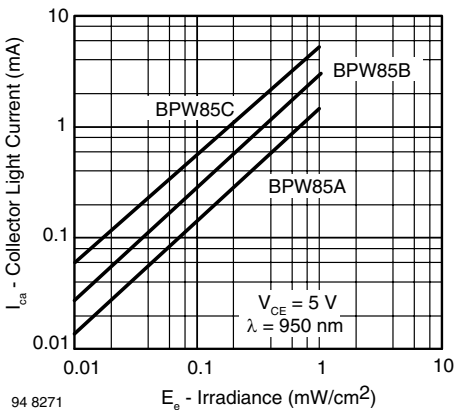


Fig. 4 - Collector Light Current vs. Irradiance

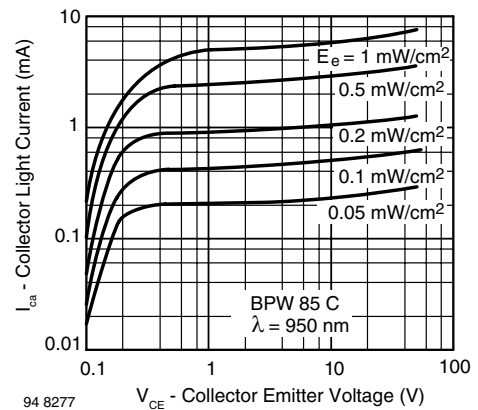


Fig. 7 - Collector Light Current vs. Collector Emitter Voltage

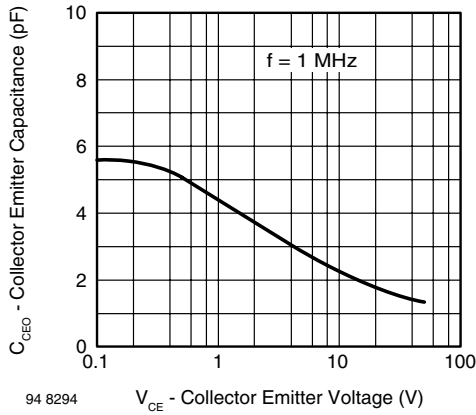


Fig. 8 - Collector Emitter Capacitance vs. Collector Emitter Voltage

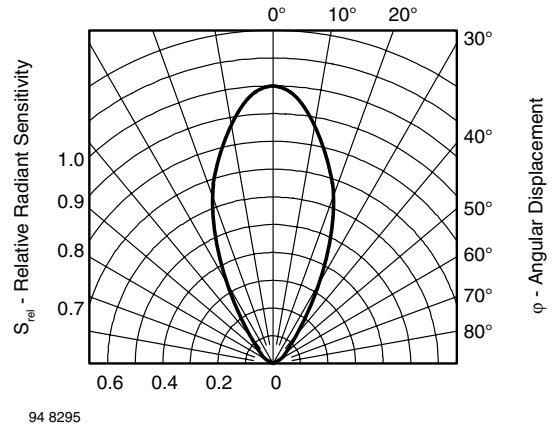


Fig. 11 - Relative Radiant Sensitivity vs. Angular Displacement

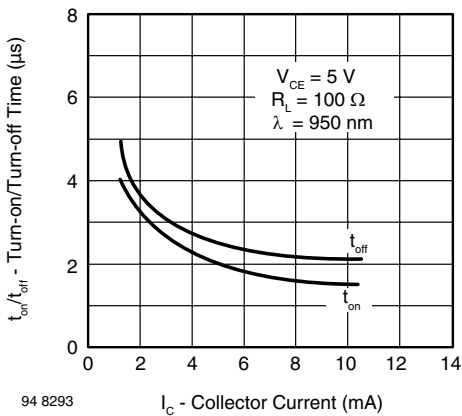


Fig. 9 - Turn-on/Turn-off Time vs. Collector Current

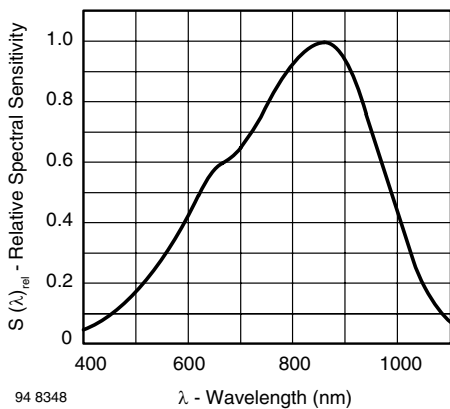


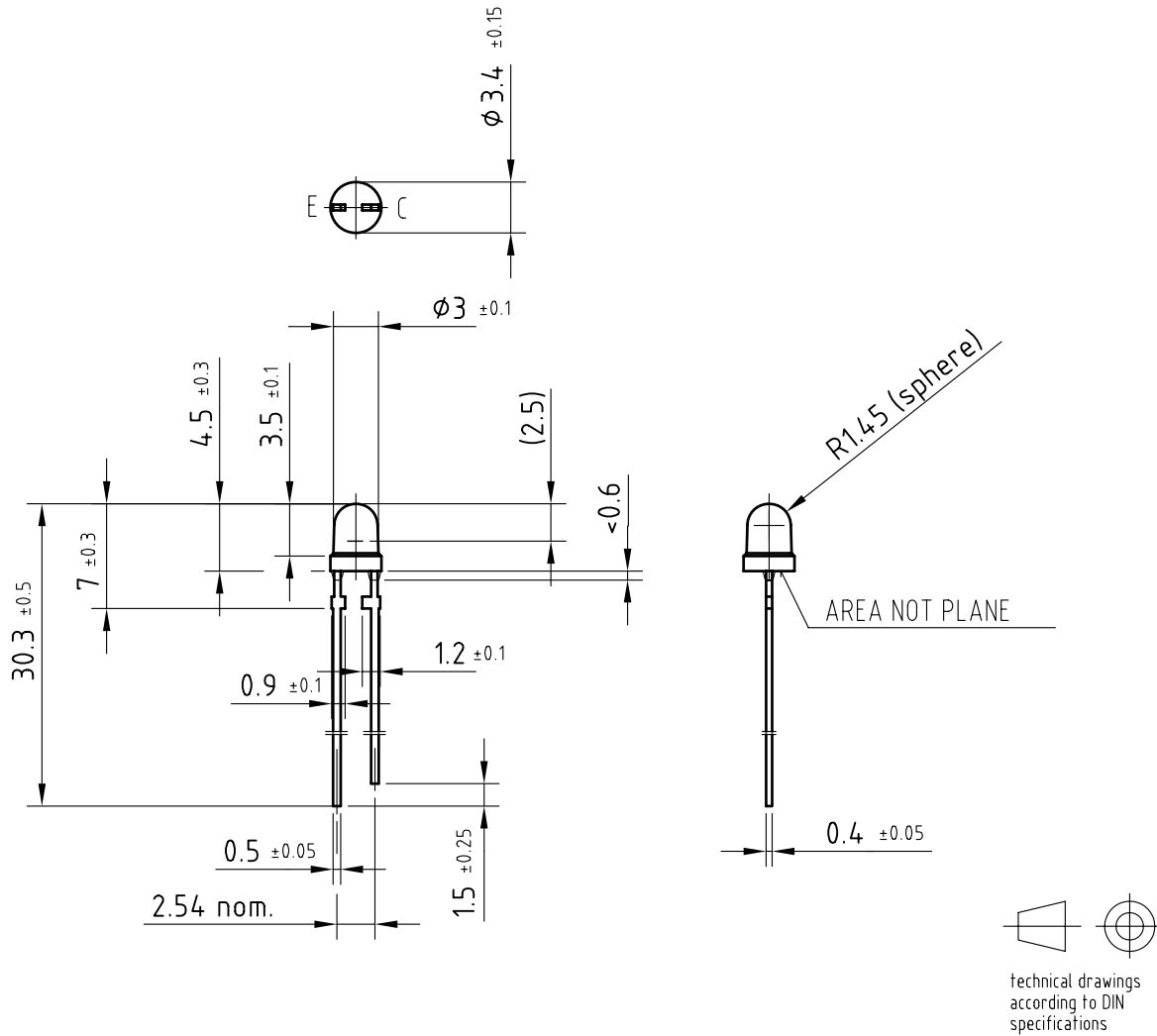
Fig. 10 - Relative Spectral Sensitivity vs. Wavelength

BPW85A, BPW85B, BPW85C

Vishay Semiconductors Silicon NPN Phototransistor, RoHS Compliant



PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5054.01-4

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96 12190



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